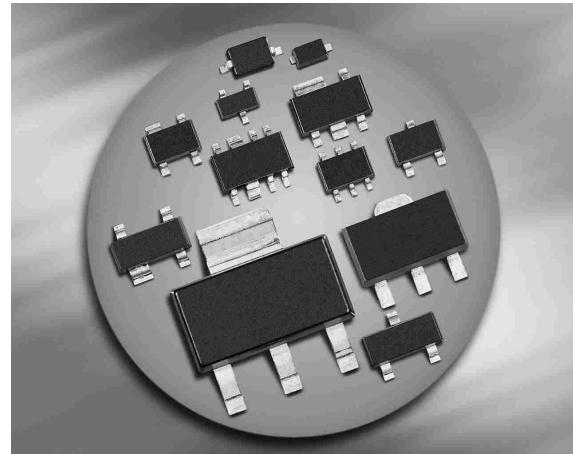
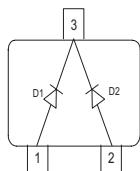


### Silicon Variable Capacitance Diode

- For FM radio tuner with extended frequency band
- High tuning ratio at low supply voltage (car radio)
- Monolithic chip (common cathode) for perfect dual diode tracking
- Good linearity for C- V curve
- High figure of merit
- Pb-free (RoHS compliant) package



### BB914



Type	Package	Configuration	$L_S$ (nH)	Marking
BB914	SOT23	common cathode	1.8	SM

**Maximum Ratings** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified

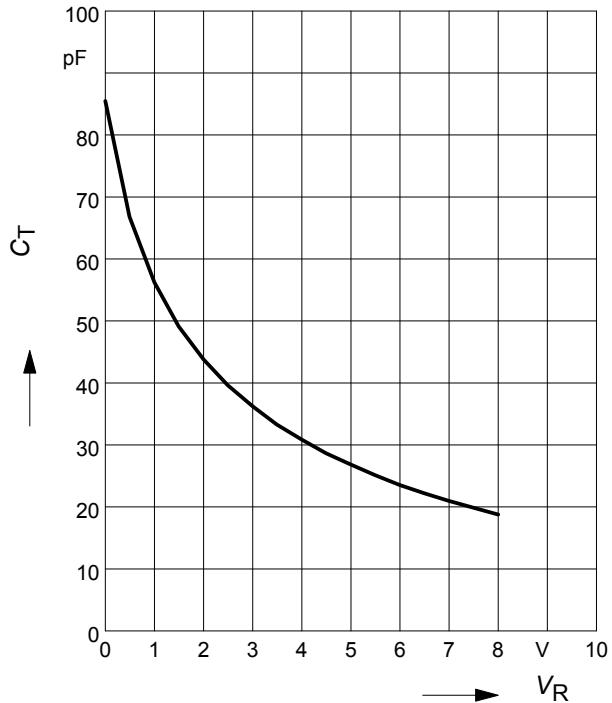
Parameter	Symbol	Value	Unit
Diode reverse voltage	$V_R$	18	V
Peak reverse voltage ( $R \geq 5\text{k}\Omega$ )	$V_{RM}$	20	
Forward current	$I_F$	50	mA
Operating temperature range	$T_{op}$	-55 ... 125	°C
Storage temperature	$T_{stg}$	-55 ... 150	

**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified

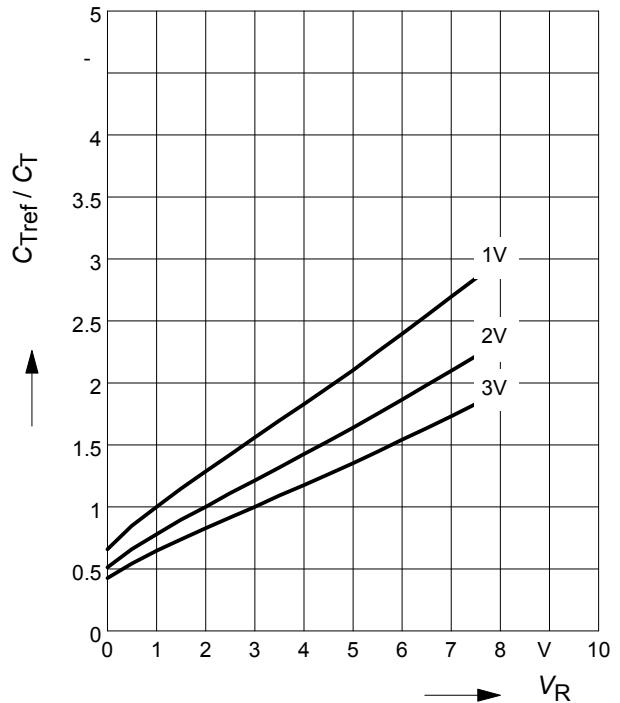
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>DC Characteristics</b>					
Reverse current $V_R = 16 \text{ V}$	$I_R$	-	-	20	nA
$V_R = 16 \text{ V}, T_A = 85^\circ\text{C}$		-	-	200	
<b>AC Characteristics</b>					
Diode capacitance $V_R = 2 \text{ V}, f = 1 \text{ MHz}$	$C_T$	42.5	43.75	45	pF
$V_R = 8 \text{ V}, f = 1 \text{ MHz}$		17.6	18.7	19.75	
Capacitance ratio $V_R = 2 \text{ V}, V_R = 8 \text{ V}, f = 1 \text{ MHz}$	$C_{T2}/C_{T8}$	2.28	2.34	2.42	
Capacitance matching <sup>1)</sup> $V_R = 2 \text{ V}, V_R = 8 \text{ V}, f = 1 \text{ MHz}$	$\Delta C_T/C_T$	-	-	1.5	%
Series resistance $V_R = 2 \text{ V}, f = 100 \text{ MHz}$	$r_S$	-	0.28	-	$\Omega$

<sup>1)</sup>For details please refer to Application Note 047.

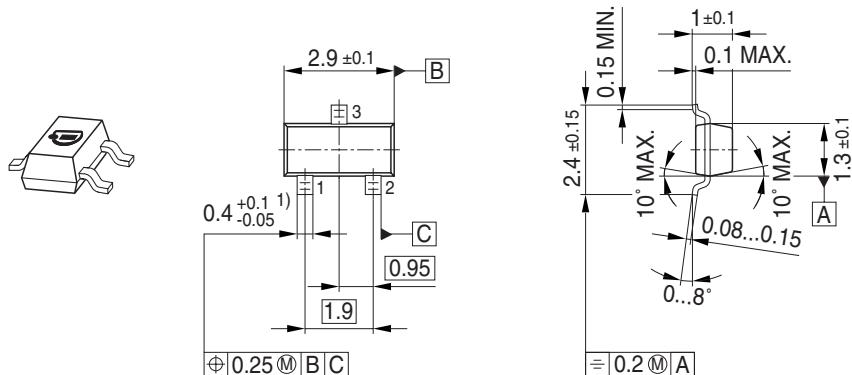
**Diode capacitance  $C_T = f (V_R)$**   
 $f = 1\text{MHz}$



**Capacitance ratio  $C_{T\text{ref}}/C_T = f (V_R)$**   
 $f = 1\text{MHz}$

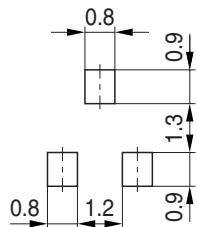


## Package Outline

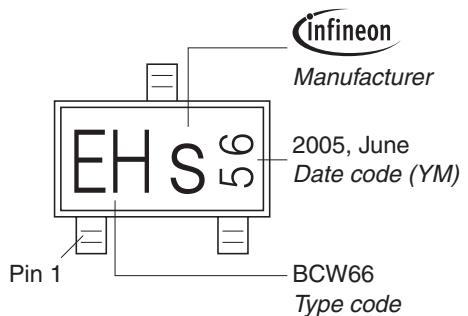


1) Lead width can be 0.6 max. in dambar area

## Foot Print

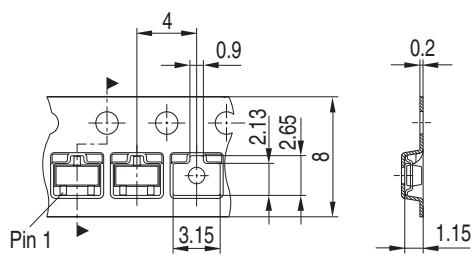


## Marking Layout (Example)



## Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel  
 Reel ø330 mm = 10.000 Pieces/Reel



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